

## R-C Thermal Model Parameters

### DESCRIPTION

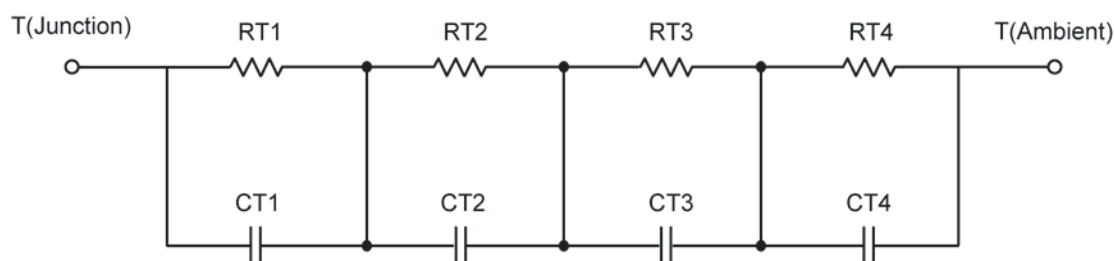
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

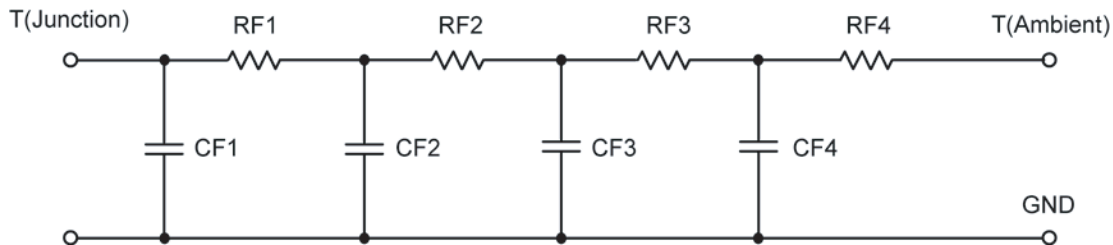
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	55.7768	N/A	12.6236
RT2	27.6343	N/A	5.1966
RT3	28.6623	N/A	6.3099
RT4	7.9266	N/A	20.8699
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.6762	N/A	7.6376 m
CT2	108.3584 m	N/A	245.7523 u
CT3	12.2944 m	N/A	10.8991 m
CT4	865.6593 u	N/A	47.9345 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	9.9293	N/A	5.5579
RF2	35.6105	N/A	17.6774
RF3	23.6406	N/A	8.2896
RF4	50.8206	N/A	13.4751
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	991.3878 $\mu$	N/A	239.4860 $\mu$
CF2	11.0310 m	N/A	3.5233 m
CF3	139.4146 m	N/A	12.8456 m
CF4	1.7139	N/A	58.7674 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

